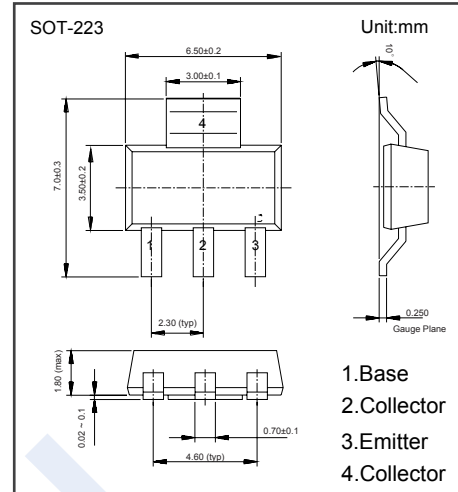


## PNP Transistors

## FZT549 (KZT549)

## ■ Features

- Collector Current Capability  $I_C = -1A$
- Collector Emitter Voltage  $V_{CE0} = -30V$

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-35	V
Collector - Emitter Voltage	$V_{CEO}$	-30	
Emitter - Base Voltage	$V_{EBO}$	-5	
Collector Current - Continuous	$I_C$	-1	A
Collector Current - Pulse	$I_{CP}$	-2	
Collector Power Dissipation	$P_C$	2	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = -100 \mu A, I_E = 0$	-35			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = -10 mA, I_B = 0$	-30			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -30 V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 A, I_B = -100mA$ (Note.1)			-0.5	V
		$I_C = -2 A, I_B = -200mA$ (Note.1)			-0.75	
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 A, I_B = -100mA$ (Note.1)			-1.25	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	$V_{CE} = -2V, I_C = -1A$ (Note.1)			-1	
DC current gain (Note.1)	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -50mA$	70			
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -500mA$	100		300	
	$h_{FE(3)}$	$V_{CE} = -2V, I_C = -1 A$	80			
	$h_{FE(4)}$	$V_{CE} = -2V, I_C = -2 A$	30			
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, f = 10MHz$			10	pF
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -100mA, f = 100MHz$	100			MHz

Note.1: Pulse width=300us. Duty cycle  $\leq 2\%$